Is Now Part of

ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at
www.onsemi.com

www.onsemi.com

ON Semiconductor®

FDMS86500L

N-Channel PowerTrench® MOSFET
60 V, 158 A, 2.5 mΩ

Features

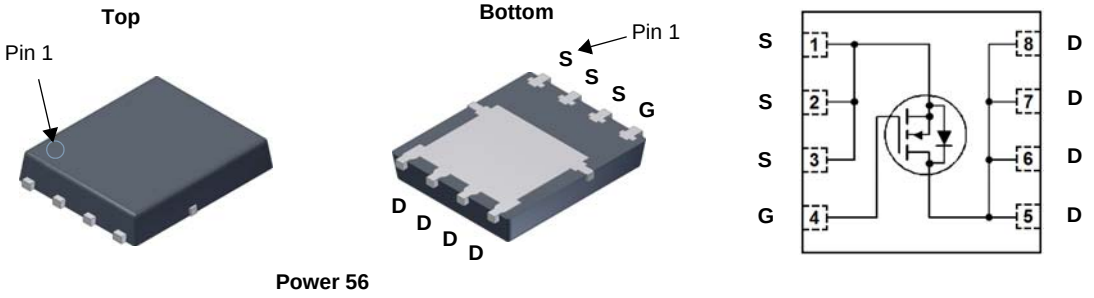
- Max $r_{DS(on)}$ = 2.5 mΩ at V_{GS} = 10 V, I_D = 25 A
- Max $r_{DS(on)}$ = 3.7 mΩ at V_{GS} = 4.5 V, I_D = 20 A
- Advanced Package and Silicon combination for low $r_{DS(on)}$ and high efficiency
- Next generation enhanced body diode technology, engineered for soft recovery
- MSL1 robust package design
- 100% UIL tested
- RoHS Compliant

General Description

This N-Channel MOSFET has been designed specifically to improve the overall efficiency and to minimize switch node ringing of DC/DC converters using either synchronous or synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low $r_{DS(on)}$, fast switching speed and body diode reverse recovery performance.

Applications

- Primary Switch in Isolated DC-DC
- Synchronous Rectifier
- Load Switch



Power 56

MOSFET Maximum Ratings T_A = 25 °C unless otherwise noted.

Symbol	Parameter			Ratings	Units
V_{DS}	Drain to Source Voltage			60	V
V_{GS}	Gate to Source Voltage			±20	V
I_D	Drain Current -Continuous	T_C = 25 °C	(Note 5)	158	A
	-Continuous	T_C = 100 °C	(Note 5)	100	
	-Continuous	T_A = 25 °C	(Note 1a)	25	
	-Pulsed		(Note 4)	799	
E_{AS}	Single Pulse Avalanche Energy		(Note 3)	240	mJ
P_D	Power Dissipation	T_C = 25 °C		104	W
	Power Dissipation	T_A = 25 °C	(Note 1a)	2.5	
T_J, T_{STG}	Operating and Storage Junction Temperature Range			-55 to +150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	1.2	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	50	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMS86500L	FDMS86500L	Power 56	13 ”	12 mm	3000 units

Semiconductor Components Industries, LLC, 2016
November, 2016, Rev. 1.5

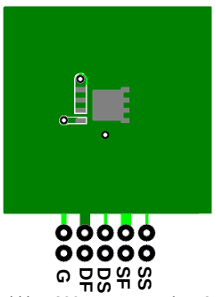
Publication Order Number:
FDMS86500L

Electrical Characteristics T_J = 25 °C unless otherwise noted.

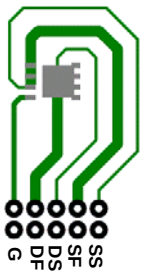
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250 μA, V_{GS} = 0 V	60			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25 °C		30		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 48 V, V_{GS} = 0 V			1	μA
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±20 V, V_{DS} = 0 V			±100	nA
On Characteristics						
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250 μA	1	1.8	3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25 °C		-7		mV/°C
$r_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10 V, I_D = 25 A		2.1	2.5	mΩ
		V_{GS} = 4.5 V, I_D = 20 A		2.9	3.7	
		V_{GS} = 10 V, I_D = 25 A, T_J = 125 °C		3.1	3.7	
g_{FS}	Forward Transconductance	V_{DS} = 5 V, I_D = 20 A		95		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 30 V, V_{GS} = 0 V, f = 1 MHz		9420	12530	pF
C_{oss}	Output Capacitance			1470	1955	pF
C_{rss}	Reverse Transfer Capacitance			50	80	pF
R_g	Gate Resistance		0.1	1.1	3.0	Ω
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 30 V, I_D = 25 A, V_{GS} = 10 V, R_{GEN} = 6 Ω		27	43	ns
t_r	Rise Time			16	28	ns
$t_{d(off)}$	Turn-Off Delay Time			63	100	ns
t_f	Fall Time			7.8	16	ns
Q_g	Total Gate Charge	V_{GS} = 0 V to 10 V; V_{DD} = 30 V, I_D = 25 A		117	165	nC
Q_g	Total Gate Charge	V_{GS} = 0 V to 4.5 V; V_{DD} = 30 V, I_D = 25 A		54	108	nC
Q_{gs}	Gate to Source Charge			26.6		nC
Q_{gd}	Gate to Drain “Miller” Charge			11.5		nC
Drain-Source Diode Characteristics						
I_s	Continuous Drain to Source Diode Forward Current	T_C = 25 °C			80	A
$I_{s,\ pluse}$	Pluse Drain to Source Diode Forward Current	T_C = 25 °C			799	A
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0 V, I_S = 2.1 A (Note 2)		0.68	1.2	V
		V_{GS} = 0 V, I_S = 25 A (Note 2)		0.79	1.3	
t_{rr}	Reverse Recovery Time	I_F = 25 A, di/dt = 100 A/μs		54	87	ns
Q_{rr}	Reverse Recovery Charge			42	67	nC
t_{rr}	Reverse Recovery Time	I_F = 25 A, di/dt = 300 A/μs		46	73	ns
Q_{rr}	Reverse Recovery Charge			84	134	nC

Notes:

1. $R_{\theta JA}$ is determined with the device mounted on a 1 in^2 pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta CA}$ is determined by the user's board design.



a) 50 °C/W when mounted on a 1 in^2 pad of 2 oz copper



b) 125 °C/W when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0%.
3. E_{AS} of 240 mJ is based on starting T_J = 25 °C, L = 0.3 mH, I_{AS} = 40 A, V_{DD} = 54 V, V_{GS} = 10 V. 100% test at L = 0.1 mH, I_{AS} = 66 A.
4. Pulsed Id please refer to Fig 11 SOA graph for more details.
5. Computed continuous current limited to Max Junction Temperature only, actual continuous current will be limited by thermal & electro-mechanical application board design.

Typical Characteristics T_J = 25 °C unless otherwise noted.

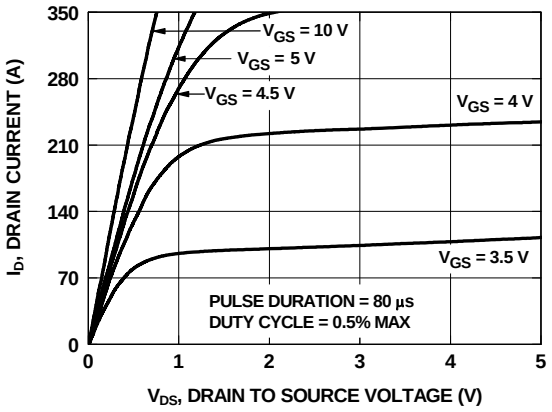


Figure 1. On-Region Characteristics

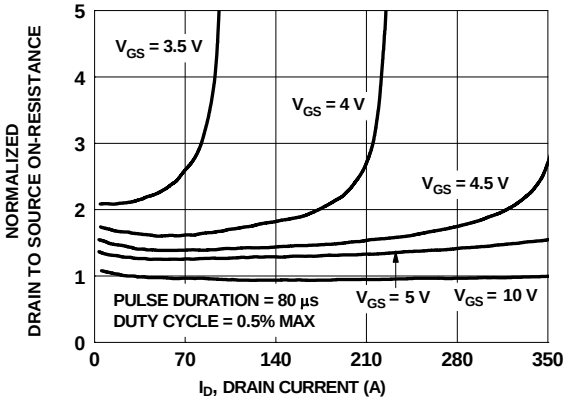


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

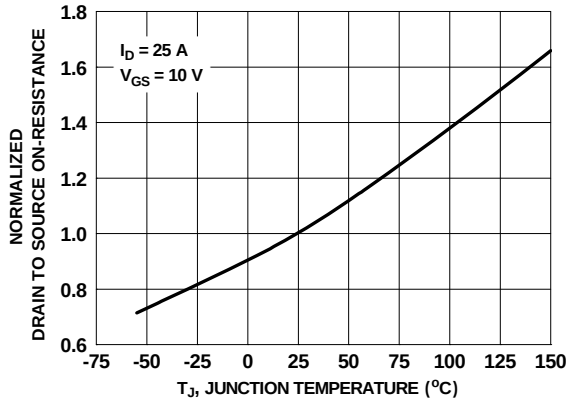


Figure 3. Normalized On-Resistance vs. Junction Temperature

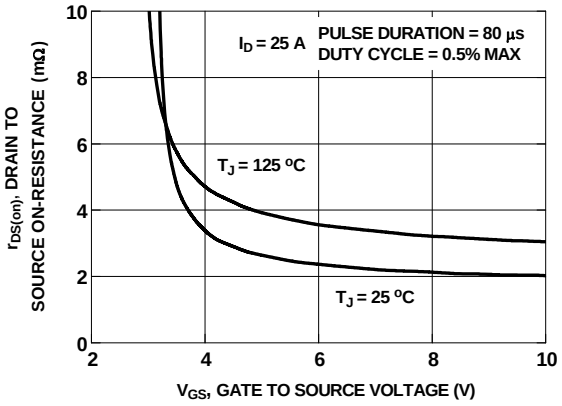


Figure 4. On-Resistance vs. Gate to Source Voltage

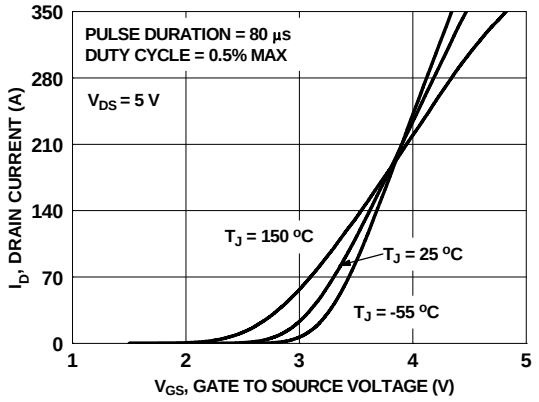


Figure 5. Transfer Characteristics

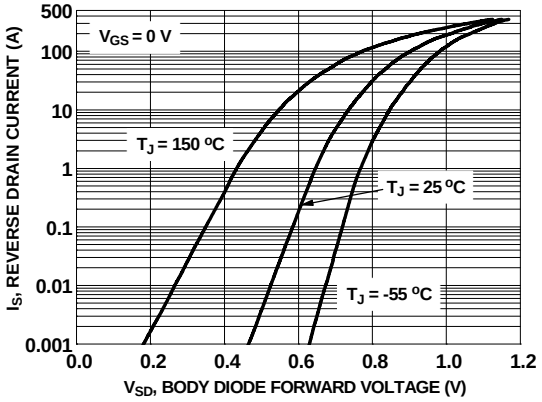


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

Typical Characteristics T_J = 25 °C unless otherwise noted.

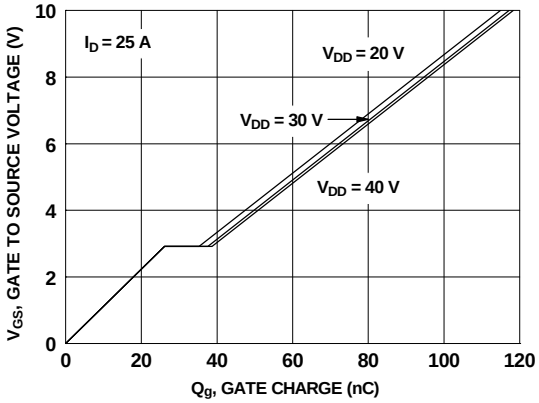


Figure 7. Gate Charge Characteristics

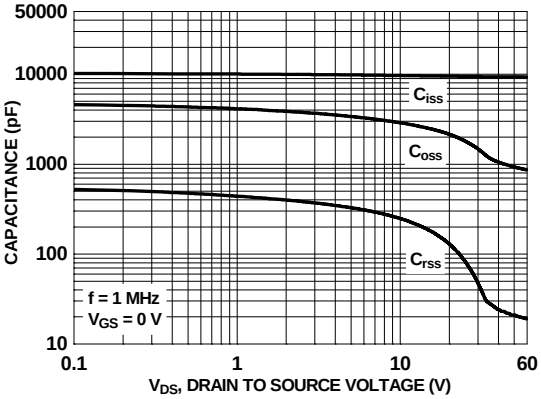


Figure 8. Capacitance vs. Drain to Source Voltage

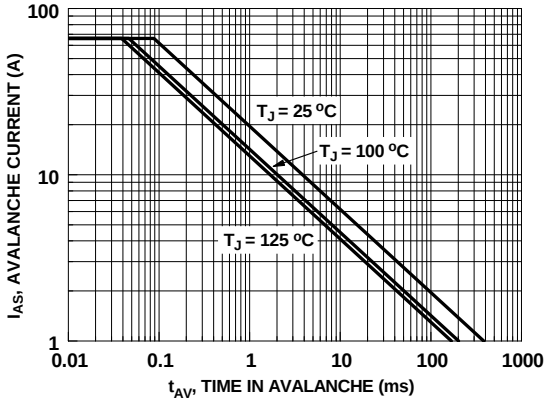


Figure 9. Unclamped Inductive Switching Capability

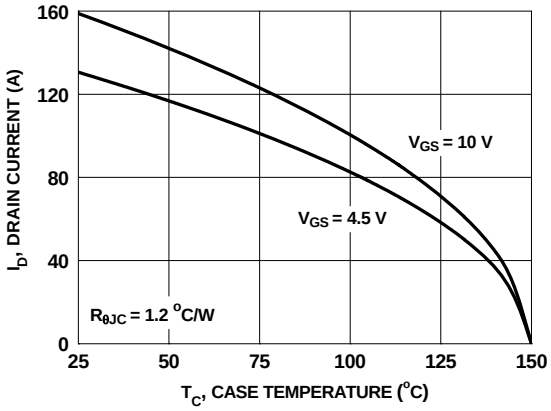


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

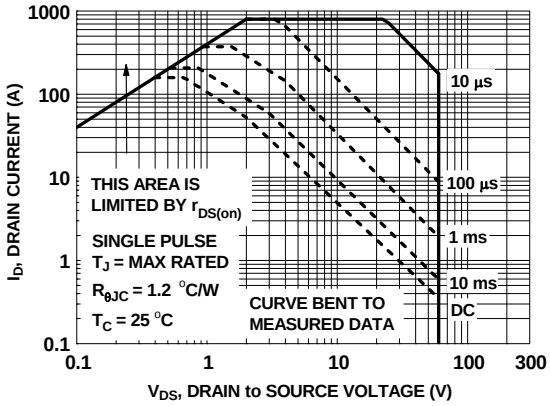


Figure 11. Forward Bias Safe Operating Area

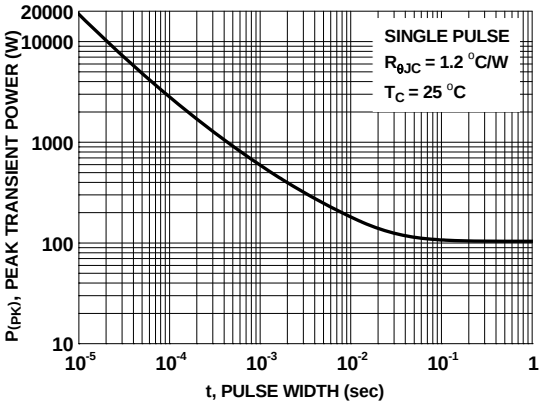


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics T_J = 25 °C unless otherwise noted.

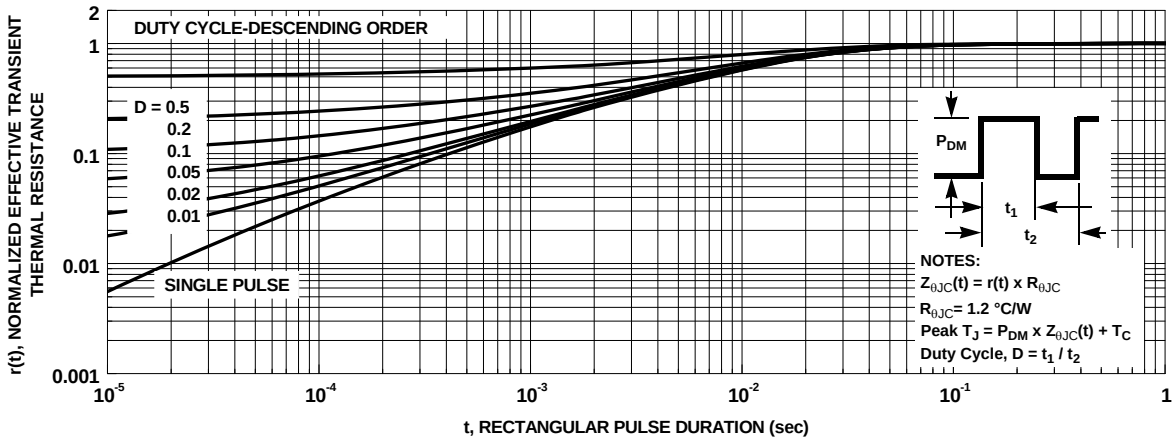
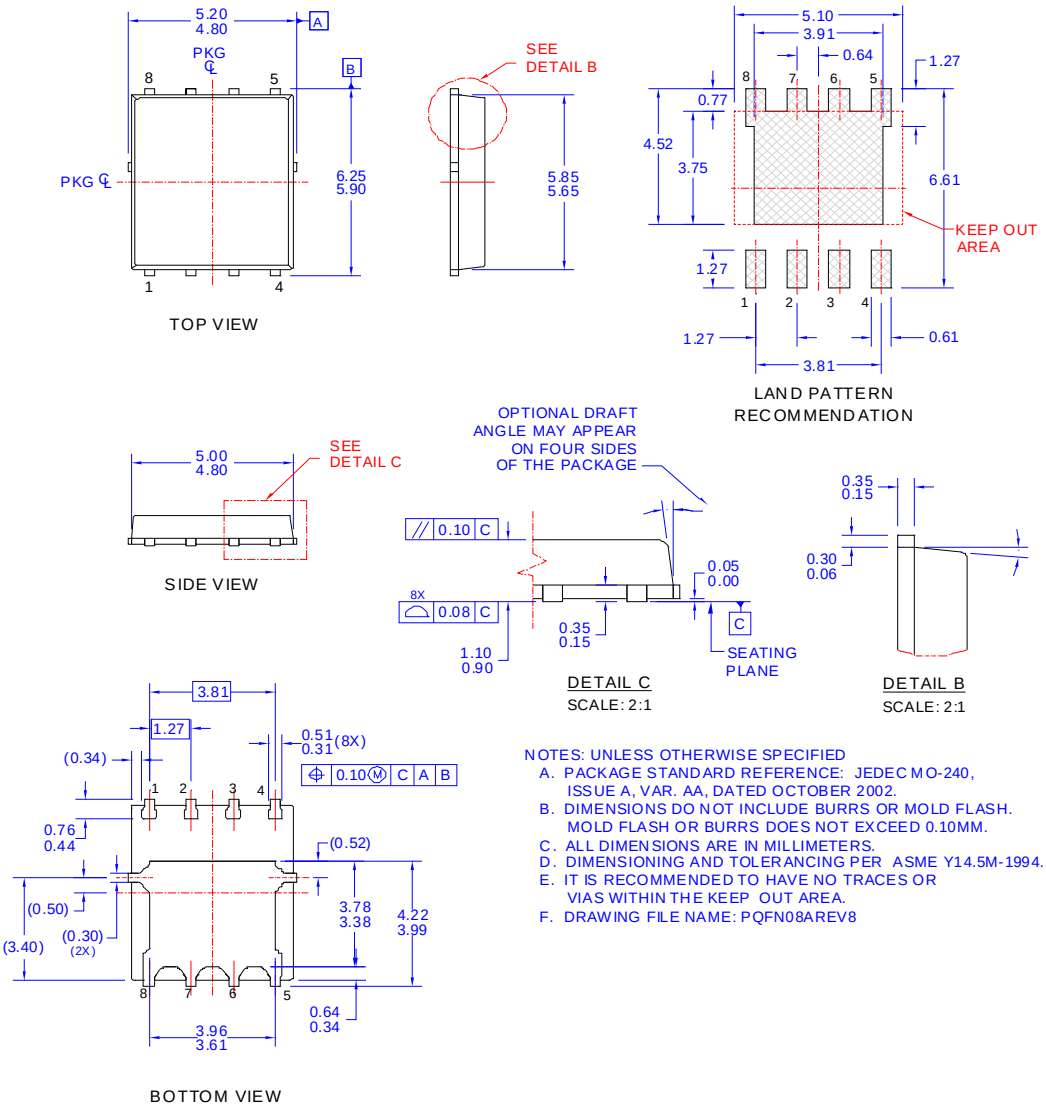


Figure 13. Junction-to-Case Transient Thermal Response Curve

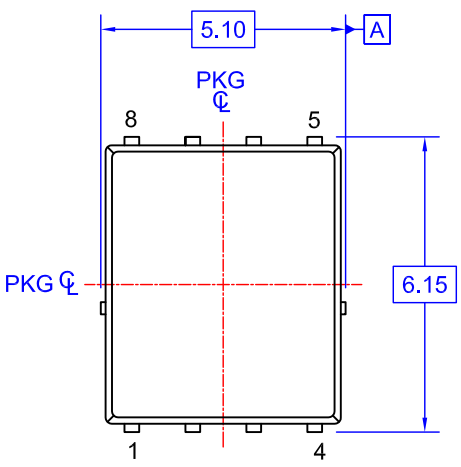
Dimensional Outline and Pad Layout



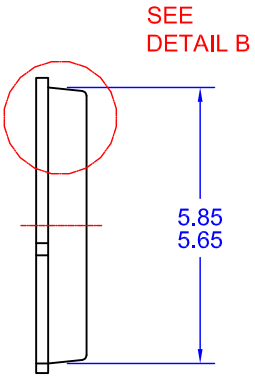
NOTES: UNLESS OTHERWISE SPECIFIED

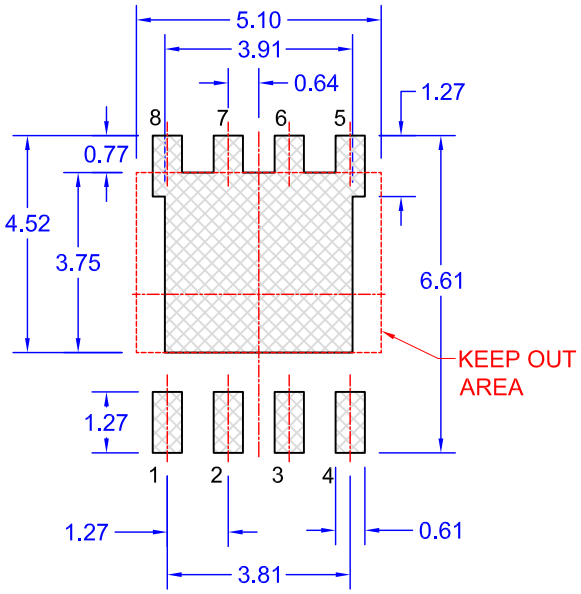
A. PACKAGE STANDARD REFERENCE: JEDEC MO-240, ISSUE A, VAR. AA, DATED OCTOBER 2002.
B. DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
C. ALL DIMENSIONS ARE IN MILLIMETERS.
D. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
E. IT IS RECOMMENDED TO HAVE NO TRACES OR VIAS WITHIN THE KEEP OUT AREA.
F. DRAWING FILE NAME: PQFN08AREV8

Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a Fairchild Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide terms and conditions, specifically the warranty therein, which covers Fairchild products.

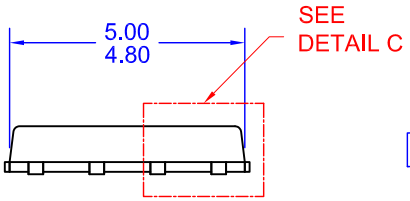


TOP VIEW

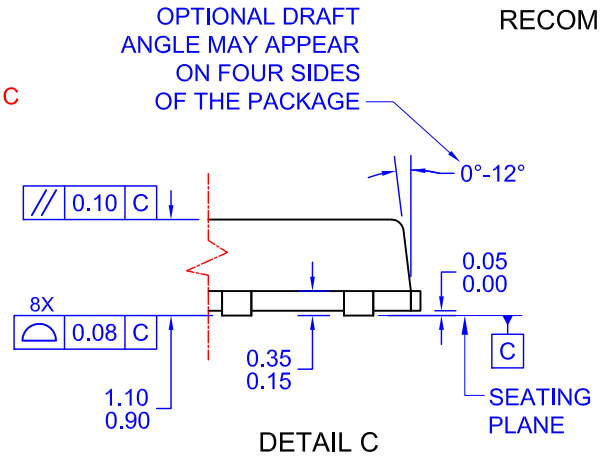




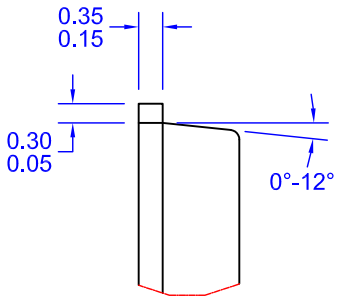
LAND PATTERN
RECOMMENDATION



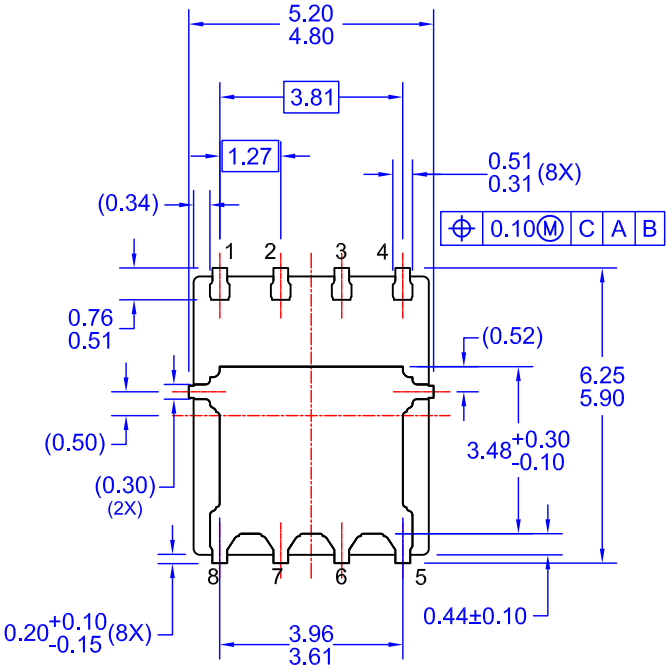
SIDE VIEW



DETAIL C
SCALE: 2:1



DETAIL B
SCALE: 2:1



BOTTOM VIEW

NOTES: UNLESS OTHERWISE SPECIFIED

A. PACKAGE STANDARD REFERENCE: JEDEC MO-240, ISSUE A, VAR. AA, DATED OCTOBER 2002.
B. DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
C. ALL DIMENSIONS ARE IN MILLIMETERS.
D. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
E. IT IS RECOMMENDED TO HAVE NO TRACES OR VIAS WITHIN THE KEEP OUT AREA.
F. DRAWING FILE NAME: PQFN08AREV10

FAIRCHILD™

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81−3−5817−1050

ON Semiconductor Website: **www.onsemi.com**

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative